Quantitative Anisotropic Analysis of Molecular Orientation in Amorphous $\text{N}_2\text{O}$ at 6 K by Infrared Multiple-Angle Incidence Resolution Spectrometry

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ABSTRACT: The existence of molecular orientational order in nanometer-thick films of molecules has long been implied by surface potential measurements. However, direct quantitative determination of the molecular orientation is challenging, especially for metastable amorphous thin films at low temperatures. This study quantifies molecular orientation in amorphous $\text{N}_2\text{O}$ at 6 K using infrared multiple-angle incidence resolution spectrometry (IR-MAIRS). The intensity ratio of the weak antisymmetric stretching vibration band of the $^{14}\text{N}^{15}\text{NO}$ isotopomer between the in-plane and out-of-plane IR-MAIRS spectra provides an average molecular orientation angle of 65° from the surface normal. No discernible change is observed in the orientation angle when a different substrate material is used (Si and Ar) at 6 K or the Si substrate temperature is changed in the range of 6−14 K. This suggests that the transient mobility of $\text{N}_2\text{O}$ during physisorption is key in governing the molecular orientation in amorphous $\text{N}_2\text{O}$.

Vapor deposition is used to prepare thin films of metals, semiconductors, and dielectrics in a vacuum, and it has wide-ranging applications across many fields for the development of functional materials.1−3 Thin-film growth of molecules (e.g., $\text{H}_2\text{O}$, CO, CO$_2$, NH$_3$, CH$_4$, and CH$_3$OH) at low temperatures is also key to understanding the formation in cold interstellar regions at around 10 K of icy dust grains, which are the starting material for the evolution of planetary systems.4−6 In 1969, Elliott et al. reported the buildup of surface potential during the condensation of water vapor on the surface of a liquid-nitrogen trap.7 The electrical properties of molecular-solid thin films at low temperatures have been widely investigated for decades, and many polar molecules develop a surface potential due to vapor deposition on a cold substrate: for example, $\text{H}_2\text{O}$,8−11 CO,8,12 NO,8 $\text{N}_2\text{O},8,13,14$ SO$_2,8$ NH$_3$,8 halocarbons (CHCl$_3$,10 CF$_3$Cl,14,15 CF$_2$Cl$_2$,15 CFCl$_3$,15 CHCl=CCl$_2$,10 and $\text{C}_6\text{H}_4\text{Cl}_2$ (ortho-dichlorobenzene)15), and organic compounds (acetone,8,10 toluene,10,14 propane,14 isopentane,14 isoprene,14 methyl formate,16,17 ethyl formate,18 2,5-dihydrofurane,18 and alcohols ($\text{C}_n\text{H}_{2n+1}\text{OH}, n = 1−5$) including isobutanol10,19−21); see also review articles.18,22 $\text{N}_2\text{O}$ has been extensively studied by Field and co-workers3,14,18,22−27 because it exhibits a clear change in its surface potential. A positive surface potential of about +11 V was reported for 355 monolayers (MLs) of polycrystalline $\text{N}_2\text{O}$ at 40 K (+32 mV per ML), which corresponds to an electric field of about 10$^5$ V m$^{-1}$.13,14,18 The authors also reported that the substrate temperature strongly affected the development of the surface potential, with a potential of only about +1 V developing for 355 MLs of polycrystalline $\text{N}_2\text{O}$ at 65 K.13,14,18 Because nonpolar molecules such as Ne, Ar, $\text{N}_2$, CO$_2$, CCl$_4$, and benzene ($\text{C}_6\text{H}_6$) do not induce surface potential evolution,8,10 the orientational order of polar molecules (dipole alignment) has been proposed as the origin of the electric potential in molecular-solid thin films at low temperatures.

Direct quantitative measurement of molecular orientation in thin solid films is challenging, especially for metastable amorphous molecular solids at low temperatures of around 10 K, despite the relevance of the orientation to the structure of icy dust in cold interstellar regions.1−6,28 Diffraction techniques using electrons or X-rays provide only limited information about the structure of amorphous materials. Although infrared (IR) spectroscopy is used to study amorphous thin films, conventional measurement techniques, such as normal-incidence transmission (Tr) and reflection−absorption (RA) at grazing incidence using a metallic substrate, observe only the surface-parallel (in-plane; IP) and surface-perpendicular (out-of-plane; OP) components of a transition moment (molecular vibration), respectively, owing...
to surface selection rules. These limitations make an accurate analysis of molecular orientation in amorphous thin films difficult. Consequently, the relationship between the structure and properties of molecular-solid thin films is poorly understood despite the accumulation of surface potential measurements.

IR multiple-angle incidence resolution spectrometry (IR-MAIRS) has recently been developed for the quantitative analysis of the molecular orientation in organic thin films. IR-MAIRS is a spectroscopic method coupled with multivariate analysis for retrieving both pure IP and OP vibration spectra from an identical sample simultaneously irrespective of its crystallinity (Figure 1 and Experimental Methods; see also refs 30 and 31 for details). The method has the unique advantage that the average molecular orientation is determined by comparing the IP to OP band intensity ratio spectra on the absorbance scale ($A_{IP}/A_{OP}$). Despite its potential usefulness, IR-MAIRS has yet to be used for amorphous molecule thin films prepared at low temperatures in a vacuum. In this study, we develop an experimental setup for in situ IR-MAIRS in low-temperature, ultrahigh-vacuum conditions (see Experimental Methods). We first validate low-temperature, ultrahigh-vacuum IR-MAIRS using amorphous CH$_4$ at 6 K, which gives similar IP and OP band intensities in IR-MAIRS because CH$_4$ is isotropic, and then show the spectroscopic signatures of anisotropic molecular orientation for amorphous N$_2$O at 6 and 14 K.

Figure 2 shows the IP and OP spectra of amorphous CH$_4$ obtained in the ν3 C–H stretching vibration band (A and B) and those of amorphous N$_2$O in the ν3 antisymmetric stretching vibration band (C and D) on a Si substrate at 6 K as a function of gas exposure time. We used a recently developed technique, MAIRS2, to obtain the IP and OP spectra with better signal-to-noise ratios than conventional MAIRS techniques (Figure 1 and Experimental Methods).

Hereafter, MAIRS2 is simply referred to as MAIRS. Similar band intensities between the IP and OP spectra at each exposure time for 1–128 min indicate the isotropic nature of CH$_4$ (Figure 2A,B). IR-MAIRS yields the intensity ratio of the surface-parallel (x- and y-directions) and surface-perpendicular (z-direction) components of a transition moment via the IP and OP spectra, and the orientation angle, $\alpha$, is defined as the uniaxial orientation angle of the transition moment, $p_z$, from the surface normal (Figure 1B). Assuming a uniaxial distribution, where the distribution of the transition moments in the x–y plane, $p_x$ and $p_y$, is averaged so that $p_z = p_z$ (Figure 1), the orientation angle $\alpha$ can be obtained by eq 1 because absorbance is proportional to the square of the transition moment (Fermi’s golden rule) (see refs 30 and 31 for details).

$$\tan \alpha = \frac{\sqrt{p_x^2 + p_y^2}}{p_z} = \frac{\sqrt{2} p_x}{p_z} = \sqrt{\frac{2A_{IP}}{A_{OP}}}$$ (1)

Unlike conventional measurement techniques, IR-MAIRS enables us to perform molecular orientation analysis without the need for optical parameters of thin sample films, because it retrieves the pure IP and OP components from the experimentally measured single-beam spectra as the least-squares solution of the classical least-squares regression equation (see Experimental Methods and refs 30–36 for details). The accuracy of IR-MAIRS can be further improved by considering the effect of the refractive index ($n$) of the thin film on the intensities of the electric fields at the optical interface along the surface-parallel ($E_x$) and surface-perpendicular ($E_z$) directions (Figure 1A). Shioya et al. theoretically deduced the correction factor to account for the intensity ratio of the electric fields at the optical interface ($E_x/E_z$) to improve the molecular orientation analysis and modified eq 1 to correct the band intensity of the OP spectrum as
\[
\alpha = \frac{2A_{IP}}{n^4 H A_{OP}} \tag{2}
\]

where \( H \) is the substrate-specific parameter \((0.33 \text{ for Si})\). In this study, typical refractive indices of 1.30 \((n^4 H = 0.943)\) and 1.32 \((n^4 H = 1.002)\) are used for the OP spectra of amorphous CH\(_4\) and N\(_2\)O, respectively, unless otherwise stated. The figures in this Letter show the corrected band intensities for the OP spectra by multiplying \( n^4 H \).

Figure 3 shows the orientation angles from the surface normal obtained from the \( \nu 3 \) band of amorphous CH\(_4\) at 6 K in Figure 2A,B. The calculated orientation angles are around \( \alpha = 56^\circ \) after 8–128 min of exposure (see also Table S1 in the Supporting Information). This angle is close to the angle of 54.7\(^\circ\), which indicates a perfectly random orientation angle. We also tested the dependence of the \( n \) value in solid CH\(_4\) on the orientation angle, using reported values of 1.28, 1.33, and 1.36. Figure 3 shows that the orientation angles are calculated as \( \alpha = 56.4^\circ \) and 53.1\(^\circ\) for \( n = 1.28 \) and 1.36 (0.886 \( \leq n^4 H \leq 1.129 \)) after 128 min of exposure, respectively (see also Table S2 in the Supporting Information). IP and OP spectra exhibit almost identical band intensity when \( n = 1.33 \), which gives \( \alpha = 54.3^\circ \) (see also Figure S3 in the Supporting Information). These results verify that the MAIRS system provides average orientation angle \( \alpha \) with an accuracy of \( \pm 2^\circ \), when the refractive index \( (n) \) is available.

The IP and OP spectra obtained by IR-MAIRS correspond to the Tr and RA spectra, respectively, in terms of shape and band positions because they are expressed as transverse (TO) energy-loss functions \( (\approx 2nk) \) and longitudinal (LO) optic energy-loss functions \( \left( = \frac{2\omega}{(\omega + k')^2} \right) \) respectively, 29–31,36,43 where \( n \) and \( k \) are the real and imaginary parts of the complex refractive index \((n + ik)\) of the thin film in IR regions, respectively. The band shape and peak position of the \( \nu 3 \) band (3009 cm\(^{-1}\)) in the IP spectra agree well with that in the Tr
spectra for amorphous CH₄ at 8 K (3010 cm⁻¹). In contrast, the OP spectra exhibit different peak positions at 3012 cm⁻¹ after 128 min of exposure (Figure 2A, B). This IP–OP peak shift originates from the TO–LO splitting, which is induced by the dispersion of n induced by the large k values, namely, the strong absorption. According to Gerakines and Hudson, the ν₃ band of amorphous CH₄ has a large k value (0.63) at 3010 cm⁻¹ compared with a typical k value (0.3) for organic compounds (e.g., CH₃(CH₂)₁₇SH) in the ν₃(CH₃) antisymmetric stretching vibration band at 2918 cm⁻¹. This is consistent with the larger IP–OP peak shift in the ν₃ band (∆ν = 3 cm⁻¹) of amorphous CH₄ than that in the ν₃(CH₃) band of cadmium stearate (∆ν ≤ 1 cm⁻¹) in IR-MAIRS.

In contrast to the MAIRS results in amorphous CH₄, the IP and OP spectra of amorphous N₂O show substantially different band shapes and intensities (Figure 2C, D). The ν₃ peak positions of the IP spectra stay at 2222 cm⁻¹ throughout the N₂O exposure for 128 min, which agrees well with the reported peak wavenumber for the Tr spectrum of amorphous N₂O at 10 K (2222 cm⁻¹). Because the Tr spectrum of crystalline N₂O has a different ν₃ peak position at 2237 cm⁻¹, the present solid N₂O samples at 6 K are amorphous throughout the 128 min gas exposure. Nevertheless, the peak positions of the OP spectra change from 2227 cm⁻¹ (∆ν = 5 cm⁻¹) to 2251 cm⁻¹ (∆ν = 29 cm⁻¹) during 1–128 min of exposure. The band intensity ratio of IP to OP spectra also changes as a function of the N₂O exposure time (see Table S3 in the Supporting Information). The IP spectra have stronger band intensities than the OP spectra (Figure 2C) during 1–32 min of exposure (8.3 × 10¹⁴–2.7 × 10¹⁶ molecules cm⁻²), whereas the A_IP/A_OP ratio decreases as the exposure time increases. The band intensity of the OP spectra eventually becomes stronger than that of the IP spectra at 128 min (1.1 × 10¹⁷ molecules cm⁻²) (Figure 2D).

In strongly absorbing bands having a k value greater than typically 1, an oscillating local electric field created by the vibrational motion of an N₂O molecule in the solid phase affects the transition dipoles in the surrounding N₂O molecules. An example of such a band is the ν₃ band of N₂O, whose k value is as large as 1.85 at ν ≈ 2222 cm⁻¹ based on the reported absorption coefficient (4πkν = 51 580 cm⁻¹). Ovchinnikov and Wight reported that the N₂O molecular vibrations in the ν₃ band are delocalized throughout amorphous N₂O by dipole–dipole interactions between the vibrations of the molecules. We therefore conclude that the molecular orientation analysis based on the strong ν₃ band is

![Figure 3](https://dx.doi.org/10.1021/acs.jpclett.0c01585)

Figure 3. Calculated average orientation angle of the transition moment from the surface normal. (A) ν₃ C–H stretching vibration band of amorphous CH₄ on a Si substrate at 6 K assuming n = 1.28 (open triangle), 1.30 (open circles), 1.33 (open square), and 1.36 (open diamond). The dashed gray guidelines are at the angle of 54.7° indicating random orientation.

![Figure 4](https://dx.doi.org/10.1021/acs.jpclett.0c01585)

Figure 4. IR-MAIRS for solid N₂O at 6 K in the region of the ν₃ (¹⁴N¹⁵NO) isotope band as a function of exposure time at 6.0 × 10⁻⁶ Pa. (A) IP spectra and (B) OP spectra. The dashed gray guidelines are at 2187 cm⁻¹.
Table 1. Summary of $A_{IP}$, $n^4H_{AOP}$, and Orientation Angle $\alpha$ for the $^{14}$N$^{15}$NO $\nu$3 Band of Amorphous N$_2$O$^a$

| experiment          | $A_{IP}$     | $n^4H_{AOP}$ | $2\times n^4H_{AOP}$ | $n^4H_{AOP}$ | $\alpha$ (deg) | error bar
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<tbody>
<tr>
<td>Si at 6 K$^b$</td>
<td>2.15 $\times 10^{-3}$</td>
<td>0.93 $\times 10^{-3}$</td>
<td>2.16</td>
<td>65.1</td>
<td>1.5</td>
<td></td>
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<tr>
<td>Si at 6 K$^b$ $n = 1.42$ $n^4H = 1.342$</td>
<td>2.15 $\times 10^{-3}$</td>
<td>1.25 $\times 10^{-3}$</td>
<td>1.87</td>
<td>61.7</td>
<td>1.7</td>
<td></td>
</tr>
<tr>
<td>Ar at 6 K$^c$</td>
<td>2.03 $\times 10^{-3}$</td>
<td>0.97 $\times 10^{-3}$</td>
<td>2.07</td>
<td>64.1</td>
<td>2.0</td>
<td></td>
</tr>
<tr>
<td>Si at 14 K$^d$</td>
<td>2.16 $\times 10^{-3}$</td>
<td>0.84 $\times 10^{-3}$</td>
<td>2.27</td>
<td>66.2</td>
<td>1.7</td>
<td></td>
</tr>
</tbody>
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$^a$The band intensities of the IP and OP spectra ($A_{IP}$ and $A_{OP}$, respectively) are calculated using the peak area of the $^{14}$N$^{15}$NO $\nu$3 band of amorphous N$_2$O. A typical refractive index of $n = 1.32$ is used for the calculation of $n^4H_{AOP}$ unless otherwise stated, where $H$ is the substrate-specific parameter ($H = 0.33$ for Si, and thus, $n^4H = 1.002$). $^{b}$Amorphous N$_2$O on a Si substrate at 6 K formed by 128 min of exposure at $6.0 \times 10^{-6}$ Pa, which corresponds to an exposure of $1.1 \times 10^{17}$ molecules cm$^{-2}$. $^{c}$Ar film was prepared on a Si substrate at 6 K by gas exposure at $7.3 \times 10^{-6}$ Pa for 2 min ($2.1 \times 10^{15}$ molecules cm$^{-2}$), and amorphous N$_2$O was subsequently formed by 128 min of exposure at $6.0 \times 10^{-6}$ Pa. $^{d}$Amorphous N$_2$O on a Si substrate at 14 K formed by 128 min of exposure at $6.0 \times 10^{-6}$ Pa.

Figure 5. IP and OP spectra of the $\nu$3 band of amorphous N$_2$O. (A and B) Amorphous N$_2$O on an Ar thin film at 6 K. The Ar film was prepared on a Si substrate at 6 K by gas exposure at $7.3 \times 10^{-6}$ Pa for 2 min, and amorphous N$_2$O was formed by 128 min of exposure at $6.0 \times 10^{-6}$ Pa. (A) $^{14}$N$^{14}$NO and (B) $^{14}$N$^{15}$NO. (C and D) Amorphous N$_2$O on a Si substrate at 14 K formed by 128 min of exposure at $6.0 \times 10^{-6}$ Pa. (C) $^{14}$N$^{14}$NO and (D) $^{14}$N$^{15}$NO. The dashed gray guidelines are at 2251 and 2222 cm$^{-1}$ (A and C) and 2187 cm$^{-1}$ (B and D), for reference.
inappropriate. Ovchinnikov and Wight also suggested that the line shape of the $\nu_3$ band depends on the macroscopic shape and orientation of the sample owing to the long-range nature of the dipole–dipole interactions. This implies that both the band shape and intensity can differ between the OP and IP spectra in IR-MAIRS, irrespective of molecular orientation.\textsuperscript{43,47} We therefore speculate that some morphological changes occur in amorphous N$_2$O as the film thickness increases during gas deposition over 1–128 min, leading to the change of the band shape and intensity of the OP spectra (Figure 2C,D).\textsuperscript{29,48}

In addition, the vibrational Stark effect can induce a frequency shift in the $\nu_3$ band of N$_2$O, because an electric field can be applied across amorphous N$_2$O film owing to anisotropic molecular orientation (dipole alignment).\textsuperscript{22,25} The vibrational Stark effect on molecular-solid thin films at low temperatures has been studied for polycrystalline N$_2$O.\textsuperscript{22,25}

Lasne et al. reported that the vibrational Stark effect can enlarge the $\Delta$/LO splitting ($\Delta$fi = 17.2 cm$^{-1}$) in polycrystalline N$_2$O, which can account for about 30% (5.2 cm$^{-1}$) and 10% (1.4 cm$^{-1}$) of the total $\Delta$/LO splitting at 48 K ($\Delta$fi = 17.2 cm$^{-1}$) and 66 K ($\Delta$fi = 13.4 cm$^{-1}$), respectively.\textsuperscript{25} The vibrational Stark effect is yet to be studied for amorphous N$_2$O because of strong inhomogeneous spectral broadening by the long-range dipole–dipole interactions,\textsuperscript{24,46} which makes a reliable analysis of small shifts of the TO and LO peak positions difficult as a function of deposition temperature (typically 1–2 cm$^{-1}$ at 48–66 K for polycrystalline N$_2$O).\textsuperscript{25} IR-MAIRS is potentially useful to study the TO-LO splitting, because it can obtain TO and LO energy-loss functions as IP and OP spectra, respectively, from an identical sample irrespective of its crystallinity. However, a comprehensive understanding of the shape and intensity in the $\nu_3$ band of the IP and OP spectra for amorphous N$_2$O requires a more detailed future investigation. Both surface potential measurements and microscopic observations of nano- or micrometer scale structures of amorphous N$_2$O are highly desirable to elucidate the influences of the vibrational Stark effect and long-range dipole–dipole interactions on the IP and OP spectra, which are beyond the scope of this Letter.

To obtain information about molecular orientation, we thus focused on the weak $\nu_3$ band of the $^{14}$N$^{15}$NO isotopomer at 2187 cm$^{-1}$.\textsuperscript{16} The $^{14}$N$^{15}$NO $\nu_3$ band is spectrally isolated and off-resonance with the major $^{14}$N$^{14}$NO $\nu_3$ band, and its concentration (0.37%)\textsuperscript{39} is sufficiently low for intermolecular vibrational coupling to be ignored (Figure 4). Therefore, the $\nu_3$ band of the $^{14}$N$^{15}$NO isotopomer can be regarded as an uncoupled localized vibration, and its transition moment direction reflects the molecular orientation of $^{14}$N$^{15}$NO molecules in amorphous N$_2$O. The $\nu_3$ band of the $^{15}$N$^{15}$NO isotopomer was detected in the IP spectrum after N$_2$O exposure for 16–32 min (Figure 4A), although the corresponding OP spectrum does not show a peak (Figure 4B). The $^{14}$N$^{15}$NO $\nu_3$ band appeared in the OP spectra after 64–128 min of exposure of N$_2$O; however, their band intensities are weaker than those in the IP spectra. These results show that the IP component of the transition moment of the $^{14}$N$^{15}$NO $\nu_3$ band is stronger than the OP component in amorphous N$_2$O at 6 K throughout the 16–128 min of exposure. The peak positions in the $^{15}$N$^{15}$NO $\nu_3$ band are similar between the IP and OP spectra at 2187 cm$^{-1}$ (Figure 4),\textsuperscript{39,46} indicating a negligible contribution of intermolecular vibrational coupling. Hence, the intensity ratio of the $^{15}$N$^{15}$NO $\nu_3$ band between the IP and OP spectra provides the molecular orientation angle. The orientation angle, $\alpha$, was calculated as 61.1° ± 1.5° from the surface normal using eq 2 (Table 1).

The present MAIRS results thus quantitatively show that there is an anisotropic molecular orientation even in an amorphous material at 6 K. The obtained orientation angle $\alpha$ in amorphous N$_2$O is an average over the area irradiated by polarized IR light (about 20 mm diameter). For reference, we tested the dependence of the $\alpha$ value in amorphous N$_2$O on the orientation angle, using a reported value of 1.42 for polycrystalline N$_2$O (Table 1).\textsuperscript{39} The orientation angle is calculated as $\alpha = 61.7° ± 1.5°$, which is still greater than 54.7° indicating random orientation. Note that the refractive index of the amorphous N$_2$O in this study should be close to the reported value in Hudson et al. ($n = 1.32$),\textsuperscript{39} because the pressures for N$_2$O exposure are similar to each other at $10^{-6}$–$10^{-5}$ Pa.

To investigate the effect of the substrate on the molecular orientation in amorphous N$_2$O, we prepared thin films of Ar on the Si substrate at 6 K by gas deposition at 7.3 × 10$^{-6}$ Pa for 2 min (2.1 × 10$^{15}$ molecules cm$^{-2}$) before the formation of amorphous N$_2$O. For reference, there are about 1.4 × 10$^{15}$ molecules cm$^{-2}$ on the surface of crystalline Ar, considering that there are four molecules in a unit cell with lattice parameters of $a = 5.30$ Å.\textsuperscript{50} Hence, 2.1 × 10$^{15}$ molecules cm$^{-2}$ correspond to about 1 ML, which is suitable for investigating the influence of the substrate–adsorbate interaction without changing the surface morphology significantly. Figure 5 shows the IP and OP spectra in the $\nu_3$ band region of (A) $^{14}$N$^{14}$NO and (B) $^{14}$N$^{15}$NO in amorphous N$_2$O on the Ar thin film at 6 K. Because the thickness of the Ar film (about 1 ML) is much smaller than that of the amorphous N$_2$O (about 100 ML), the refractive index of amorphous N$_2$O ($n = 1.32$) was used for the OP spectra as a good approximation (Table 1). The IP and OP spectra of $^{14}$N$^{14}$NO and $^{14}$N$^{15}$NO isotopomers have band shapes and intensities almost identical to the corresponding spectra on the bare Si substrate (Figures 2D and 4), and the $^{14}$N$^{15}$NO $\nu_3$ band exhibits a similar orientation angle ($\alpha = 64.1° ± 2.0°$) (Table 1). These results suggest that the molecular orientation is determined by physisorption of N$_2$O molecules on the surface through van der Waals forces in this study. The independence of the electrical properties in molecular solids from the substrate is also reported in previous studies.\textsuperscript{8,18,24}

Because N$_2$O is a triatomic linear molecule, an orientation parallel to the surface is thermodynamically preferred for physisorbed N$_2$O because of the large contact area with the surface. The physical vapor deposition of linear-chain molecules (e.g., paraffin and stearic acid) on a cold substrate generally results in a parallel molecular orientation to achieve a large surface contact area.\textsuperscript{151,152} Compared with linear-chain molecules, the energy difference for physisorbed N$_2$O between parallel and perpendicular orientations to the surface is much smaller. Nevertheless, the small anisotropic difference in the physisorption energy of N$_2$O is attributed to the slightly parallel molecular orientation (65°) in amorphous N$_2$O, especially at a low temperature of 6 K.

From the kinetic point of view, the formation of metastable amorphous N$_2$O at 6 K shows that the incoming N$_2$O molecules cannot diffuse and settle on the most energetically favorable crystalline sites until new monomers are adsorbed and molecular motion ceases.\textsuperscript{53} Considering the random orientation of N$_2$O molecules in the gas phase, the transient diffusion of adsorbed N$_2$O before it is fully thermalized on the
surface leads to the parallel molecular orientation ($\alpha = 65^\circ$) in amorphous N$_2$O at 6 K. When the N$_2$O deposition experiment is performed on the Si substrate at 14 K, a similar orientation angle ($\alpha = 66.2^\circ \pm 1.7^\circ$) is obtained for the $^{14}$N$^{15}$NO ν3 band of amorphous N$_2$O (Figure S5D; see also Table S4 in the Supporting Information). Hence, at substrate temperatures of 6−14 K, the transient mobility of the adsorbed N$_2$O molecules is driven by the incident kinetic temperature (295 K) and the physisorption energy on the surface, rather than the substrate temperature. Thus, molecular dynamics during physisorption is a key factor in the molecular orientation of amorphous N$_2$O. The physisorption energy of N$_2$O should lie in the range of 1000−3500 K, considering the physisorption energy of the N$_2$O−N$_2$O dimer (903−929 K).$^{14}$ The desorption energy of polycrystalline CO$_2$ (2300−3500 K),$^{55,56}$ and similar desorption temperatures between polycrystalline CO$_2$ and N$_2$O at substrate temperatures of 70−95 K.$^{13,18,55,56}$ Further evaluation of the role of the physisorption process in the observed parallel molecular orientation requires molecular dynamics simulations. Above 22 K, N$_2$O starts to crystallize, which parallel molecular orientation requires molecular dynamics during physisorption to achieve the base pressure after deposition is about 5 min. For reference, there are about 1.2×10$^{15}$, 1.4×10$^{15}$, and 1.8×10$^{15}$ molecules cm$^{-2}$ s$^{-1}$ for CH$_4$ (99.995%, Nihonsanso Co., Ltd.), N$_2$O (99.9%, Koike medical Co., Ltd.), and Ar (99.9995%, Air Water Inc.) were introduced onto the Si substrate at 6 K by background deposition at 1.0×10$^{-5}$ Pa, measured using a crystal ion gauge (N-336MX, Canon Anelva). Molecular-solid thin films are formed on both sides of the Si substrate. The actual pressures for CH$_4$, N$_2$O, and Ar were calculated as 6.7×10$^{-5}$, 6.0×10$^{-6}$, and 7.3×10$^{-6}$ Pa, respectively; using the gas correction factors for CH$_4$ (1.49), N$_2$O (1.66), and Ar (1.37).$^{35}$ The fluxes of CH$_4$, N$_2$O, and Ar were estimated as 2.6×10$^{13}$, 1.4×10$^{13}$, and 1.8×10$^{13}$ molecules cm$^{-2}$ s$^{-1}$, respectively, based on the actual pressure. For reference, there are about 1.2×10$^{15}$, 1.2×10$^{15}$, and 1.4×10$^{15}$ molecules cm$^{-2}$ on the surface of crystalline N$_2$O, CH$_4$, and Ar, respectively, considering that there are four molecules in a unit cell with lattice parameters of $a = 5.67$, $5.85$, and $5.30 \ \AA$, respectively.$^{30,31,36,36}$

IR-MAIRS allows this approach to be extended to combination studies that include surface potential measurements, and the approach is applicable to all polar molecules studied previously,$^{8−22}$ such as nonpolar molecules, including those with anisotropic molecular shapes (e.g., linear alkanes).$^{3,33,36,43}$ Further combination studies using these molecules will provide insights into the origins of the anisotropic molecular orientation and partial dipole alignment during vapor deposition of molecules on cold substrates. IR-MAIRS measurements should also help to reveal the fine structures of solid molecules (e.g., H$_2$O) that are important to astrophysics at low temperatures because many of these molecules form amorphous solids in cold interstellar regions.

## EXPERIMENTAL METHODS

### MAIRS Measurements.

For low-temperature, ultrahigh-vacuum IR-MAIRS, we built an experimental apparatus comprising a vacuum sample chamber and a Fourier transform infrared (FTIR) spectrometer. The vacuum sample chamber was evacuated to ultrahigh-vacuum conditions (base pressure 10$^{-7}$ Pa) using a turbo molecular pump (STP-451, 480 L s$^{-1}$ for N$_2$O, Edwards). A Si(111) substrate (40×40×1 mm, Pier Optics Co., Ltd.) was mounted on a copper sample holder without removing the native oxide on the Si surface. The Si substrate and copper sample holder were connected with indium solder by ultrasonic soldering under a nitrogen atmosphere to ensure good thermal contact for cooling the Si substrate to 6 K (Figure S4).$^{32}$ The copper sample holder was connected to the cold head of a closed-cycle He refrigerator (RDG-101D, Sumitomo Heavy Industries) and installed in the vacuum sample chamber using a bore-through rotary feedthrough (KRP-152, Kitano Seiki Co., Ltd.).

The Si substrate in the chamber was installed in the sample compartment of the FTIR spectrometer (Nicolet iS50, Thermo Fisher Scientific) in transmission geometry across two ZnSe windows (f = 3 mm) in the chamber. The He refrigerator was freely rotatable by the bore-through rotary feedthrough, the angle of incidence of the IR beam (∟θ) was varied by rotating the Si substrate. The temperature of the Si substrate was measured using a Si diode sensor (DT-670, Lakeshore) placed in the copper sample holder and controlled with an accuracy of ±0.2 K using a temperature controller (Model 325, Lakeshore) and a ceramic heater (40 W).

CH$_4$ (99.99%, Nihonsanso Co., Ltd.), N$_2$O (99.9%, Koike medical Co., Ltd.), and Ar (99.9995%, Air Water Inc.) were introduced onto the Si substrate at 6 K by background deposition at 1.0×10$^{-5}$ Pa, measured using a crystal ion gauge (N-336MX, Canon Anelva). Molecular-solid thin films are formed on both sides of the Si substrate. The actual pressures for CH$_4$, N$_2$O, and Ar were calculated as 6.7×10$^{-5}$, 6.0×10$^{-6}$, and 7.3×10$^{-6}$ Pa, respectively; using the gas correction factors for CH$_4$ (1.49), N$_2$O (1.66), and Ar (1.37).$^{35}$ The fluxes of CH$_4$, N$_2$O, and Ar were estimated as 2.6×10$^{13}$, 1.4×10$^{13}$, and 1.8×10$^{13}$ molecules cm$^{-2}$ s$^{-1}$, respectively, based on the actual pressure. For reference, there are about 1.2×10$^{15}$, 1.2×10$^{15}$, and 1.4×10$^{15}$ molecules cm$^{-2}$ on the surface of crystalline N$_2$O, CH$_4$, and Ar, respectively, considering that there are four molecules in a unit cell with lattice parameters of $a = 5.67$, $5.85$, and $5.30 \ \AA$, respectively.$^{30,31,36,36}$ Typical time to achieve the base pressure after deposition is about 5 min.

For IR-MAIRS measurements, the MAIRS2 technique, which was recently developed as the second generation of MAIRS by Shioya et al.$^{12}$ was used. In MAIRS2, the IR spectra
of a sample film are collected at a fixed incident angle of $\theta = 45^\circ$ with seven polarization angles ($\phi$) from s-polarization ($\phi = 0^\circ$) to p-polarization ($\phi = 90^\circ$) in $15^\circ$ steps (Figures 1, S1, and S2), and the IP and OP spectra are calculated through the classical least-squares regression equation (see MAIRS Analysis below for details). For reference, the present apparatus can also perform other MAIRS techniques, such as pMAIRS, in which the IR spectra of a sample film on the Si substrate are collected with different incident angles, $\theta$, of $9-45^\circ$ in $5^\circ$ steps using p-polarized IR light (see ref 35, 43, and 61 for details). Compared with pMAIRS, MAIRS2 has the advantage that optical interference fringes from multiple reflections in the substrate do not appear in the absorption spectrum because of the oblique incident angle fixed at $\theta = 45^\circ$, which leads to a better signal-to-noise ratio than pMAIRS.36 The modulated IR light was passed through an angle-controllable wire-grid linear ZnSe polarizer incorporated in the spectrometer before entering the vacuum sample chamber. A mercury cadmium telluride detector was used to detect the IR light. The accumulation number of the single-beam measurements was $500 \times 373$ s for each polarization angle with a resolution of 4 cm$^{-1}$. The total measurement time was 2611 s for one IR-MAIRS measurement.

MAIRS Analysis. The basic concept of MAIRS is described by Hasegawa32 and elsewhere.30 The details of the analytical procedure in MAIRS2 used in this study are described by Shioya et al.36 The analytical expressions for MAIRS deduced from Maxwell’s equations are presented by Itoh et al.34 although it requires heavy mathematical calculations. Hence, only a brief outline is given here. The intensity of linearly polarized IR light with polarization angle $\phi$ and incident angle $\theta$ (fixed at $45^\circ$ in this study) are expressed as a linear combination of the IP and OP polarization components (Figure 1A).32,36 Thus, the experimentally measured single-beam spectra can be decomposed into the pure IP and OP components as the least-squares solution of the classical least-squares regression equation as

$$
\begin{align*}
    s_{obs,1} = \begin{pmatrix} I_{IP,1} \\ r_{IP,1} \end{pmatrix}, & \quad s_{obs,2} = \begin{pmatrix} I_{OP,1} \\ r_{OP,1} \end{pmatrix}, \\
    \vdots & \quad \vdots \\
    s_{obs,n} & \quad s_{obs,n}
\end{pmatrix}

= \begin{pmatrix} S_{IP} \\ S_{OP} \end{pmatrix} + \begin{pmatrix} U \end{pmatrix}

= (R^T R)^{-1} R^T s_{obs}
\end{align*}
$$

where $s_{obs,j}$ ($j = 1, 2, 3\ldots$) is a row vector that represents a transmission (single-beam) spectrum measured at a polarization angle of $\phi_j$ ($j = 1, 2, 3\ldots$), the collection of $s_{obs,j}$ vectors forms the matrix, and $s_{obs}$, $S_{IP}$ and $S_{OP}$ are the decomposed IP and OP single-beam spectra, respectively. $r_{IP,j}$ ($j = 1, 2, 3\ldots$) and $r_{OP,j}$ ($j = 1, 2, 3\ldots$) are weighting coefficients for $S_{IP}$ and $S_{OP}$, respectively. For example, $s_{obs,1}$ can be expressed as a linear combination of $S_{IP}$ and $S_{OP}$ as

$$
\begin{align*}
    s_{obs,1} = r_{IP,1} S_{IP} + r_{OP,1} S_{OP}
\end{align*}
$$

$R$ is a matrix of weighting coefficients for $S_{IP}$ and $S_{OP}$. $U$ is a matrix containing a nonlinear response to $R$. Therefore, nonlinear noise factors (e.g., reflected IR light) are rejected in the classical least-squares regression calculation and pooled in $U$ as the error.

For details of the deduction of $R$, we refer interested readers to the original references.32,34,36 In short, Shioya et al.36 show that $R$ depends on polarization angle $\phi$, expressed as

$$
R = \left\{ \begin{array}{c}
\gamma \cos^2 \phi_1 + \sin^2 \phi_1 \gamma (\sin^2 \theta \tan^2 \theta + \cos^2 \theta) \sin^2 \phi_1 \tan^2 \theta \\
\vdots \\
\vdots
\end{array} \right\}
$$

where $\gamma$ is defined as the intensity ratio of the s-polarized light ($S_{blank}^s$) to the p-polarized light ($S_{blank}^p$) at a wavenumber when measured without a substrate (blank). In practice, $\gamma$ can be calculated using the s- and p-polarized single-beam spectra of the background measurements with a substrate ($S_{bg}^s$ and $S_{bg}^p$, respectively) and the transmittance of the substrate for the s- and p-polarized light ($T_{sub}^s$ and $T_{sub}^p$, respectively) as

$$
\gamma \equiv \frac{S_{blank}^p}{S_{blank}^s} = \frac{S_{bg}^p T_{sub}^s}{S_{bg}^s T_{sub}^p}
$$

because $S_{bg}^s = S_{blank}^s T_{sub}^s$ and $S_{bg}^p = S_{blank}^p T_{sub}^p$. $T_{sub}^s$ and $T_{sub}^p$ can be calculated using the refractive index of the substrate (3.41 for Si).30,34,62 After obtaining the IP and OP single-beam spectra ($S_{IP}$ and $S_{OP}$), the IP and OP absorbance spectra ($A_{IP}$ and $A_{OP}$) are calculated as

$$
A_{IP} = -\log \frac{S_{IP}}{S_{IP}^{sam}}, \quad A_{OP} = -\log \frac{S_{OP}}{S_{OP}^{sam}}
$$

where the superscripts bg and sam indicate background and sample measurements, respectively.

## ASSOCIATED CONTENT

### Supporting Information

The Supporting Information is available free of charge at https://pubs.acs.org/doi/10.1021/acs.jpcl.0c01585.

Typical single-beam spectra measured at an angle of incidence of $45^\circ$ at various polarization angles from $0^\circ$ (s-polarization) to $90^\circ$ (p-polarization) in $15^\circ$ steps before the MAIRS analysis (Figures S1 and S2); IP and OP spectra of the $2\nu$ band of amorphous CH$_4$ at 6 K calculated assuming $n = 1.33$ (Figure S3); photograph of Si substrate connected with copper sample holder with indium solder by ultrasonic soldering (Figure S4); summary of $A_{IP}$, $n^4$H$_{OP}$, $\frac{2\alpha_{IP}}{n^4}$, and orientation angle $\alpha$ for the $\nu$ band of amorphous CH$_4$ on a Si substrate at 6 K (Table S1); summary of the dependence of the $n$ ($n^4$H) value on $A_{IP}$, $n^4$H$_{OP}$, $\frac{2\alpha_{IP}}{n^4}$, and orientation angle $\alpha$ for the $\nu$ band of amorphous CH$_4$ on a Si substrate at 6 K (Table S2); summary of $A_{IP}$, $n^4$H$_{OP}$, $\frac{2\alpha_{IP}}{n^4}$, and orientation angle $\alpha$ for the $^{14}$N$_{4}$NO $\nu$ band of amorphous N$_2$O on a Si substrate at 6 K (Table S3) (PDF)

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Notes

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